PHOTONIC DETECTORS INC. PACKAGE DIMENSIONS inch [mm]

Silicon Photodiode, Blue Enhanced Photovoltaic Isolated Type PDB-V101-I

WINDOW CAP

WIRE BONDS

HEADER

TO-18 HERMETIC CAN PACKAGE

0.7

0.6 0.5 0.4 0.3 0.2 0.1 0

(WELDED)

PHOTODIODE CHIP

- 0.040 [1.02]

Ø0.100 B.C.

Ģ 45

0.042 [1.06]

Ø0.019 [0.48] Ø0.016 [0.41] 3 PLACES

-0.053 [1.35] SQUARE - Ø0.0247 [Ø0.627] ACTIVE AREA

ACTIVE AREA = 0.31 mm²



FEATURES

- Low noise
- · Blue enhanced
- High shunt resistance
- · High response



The PDB-V101-I is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for low noise photovoltaic applications. Packaged in a hermetic TO-18 metal can with a flat window and isolated ground lead.

Ø0.184 [4.67]

Ø0.210 [5.33]

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Ø0.155 [3.94]

APPLICATIONS

- Instrumentation
- Industrial controls

0.198 [5.03]

0.125 [3.18]

0.500

MIN

CATHODE

ANODE

CASE GROUND

- Laser detection
- · Particle detection

SPECTRAL RESPONSE

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

					,				
S	SYMBOL	PARAMETER	MIN	MAX	UNITS	Ś			
	VBR Reverse Voltage			75	V	۲ (A			
T _{stg}		Storage Temperature	-55	+150	°C	ΓN			
T _o		Operating Temperature Range	-40	+125	°C	INISN			
	T _s Soldering Temperature*			+240	°C	SPC			
	I,	Light Current		.5	mA	Ë			
*1/16 inch from case for 3 secs max									

WAVELENGTH (nm)

600

500 700 800 900

400

000 1100 200

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)										
SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS				
I _{sc}	Short Circuit Current	H = 100 fc, 2850 K	4	4.5		mA				
I _D	Dark Current	$H = 0, V_{_{\rm R}} = 10 \text{ V}$		20	45	pА				
R _{sh}	Shunt Resistance	$H = 0, V_{_{\rm R}} = 10 \text{ mV}$	1	1.6		G W				
TC R _{SH}	RSH Temp. Coefficient	$H = 0, V_{_{\rm R}} = 10 \text{ mV}$		-8		% / °C				
C	Junction Capacitance	$H = 0, V_{_{\rm R}} = 0 V^{**}$		115		pF				
I range	Spectral Application Range	Spot Scan	350		1100	nm				
∎ p	Spectral Response - Peak	Spot Scan		950		nm				
V _{BR}	Breakdown Voltage	I = 10 m A	30	50		V				
NEP	Noise Equivalent Power	V _R = 10 mV @ Peak		2.5x10 ⁻¹⁵		W/ √Hz				
tr	Response Time	$RL = 1 KWV_{R} = 0 V$		450		nS				

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz